

## **LOW VOLTAGE ANTIFUSE DEVICE AND PROCESS**

### **ABSTRACT OF THE DISCLOSURE**

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A method of producing an antifuse includes introducing nitrogen by ion implantation means into the substrate. An oxide dielectric layer is then formed on the nitrided substrate in a wet oxidation ambient. The conditions of the ion implantation and the oxidation are controlled to generate a dielectric with uniform thickness and a

10 low breakdown voltage when subjected to a high electric field.